

#### General Description

Maxim's redesigned DG417/DG418/DG419 precision, CMOS, monolithic analog switches now feature guaranteed on-resistance matching (3 $\Omega$  max) between switches and guaranteed on-resistance flatness over the signal range (4 $\Omega$  max). These switches conduct equally well in either direction and guarantee low charge injection, low power consumption, and an ESD tolerance of 2000V minimum per Method 3015.7. The new design offers low off-leakage current over temperature (less than 5nA at +85°C).

The DG417/DG418 are single-pole/single-throw (SPST) switches. The DG417 is normally closed, and the DG418 is normally open. The DG419 is singlepole/double-throw (SPDT) with one normally closed switch and one normally open switch. Switching times are less than 175ns max for ton and less than 145ns max for toff. Operation is from a single +10V to +30V supply, or bipolar  $\pm 4.5 \text{V}$  to  $\pm 20 \text{V}$  supplies. The improved DG417/DG418/DG419 are fabricated with a 44V silicon-gate process.

#### Applications

Sample-and-Hold Circuits Communications Systems Test Equipment Battery-Operated Systems Modems Fax Machines Guidance and Control Systems PBX, PABX Audio Signal Routing Military Radios

#### New Features

- Plug-In Upgrades for Industry-Standard DG417/DG418/DG419
- **♦ Improved Rps(ON) Match Between Channels**  $(3\dot{\Omega} \text{ max}, DG4\dot{1}9 \text{ only})$
- Guaranteed RFLAT(ON) Over Signal Range (4Ω max)
- ♦ Improved Charge Injection (10pC max)
- **♦ Improved Off-Leakage Current Over Temperature** (<5nA at +85°C)
- **♦ Withstand Electrostatic Discharge (2000V min)** per Method 3015.7

Existing Features

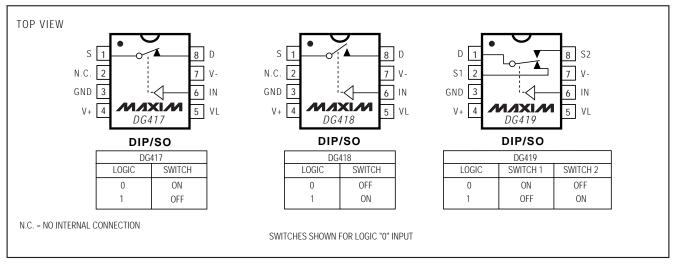
- Low R<sub>DS(ON)</sub> (35Ω max)
- Single-Supply Operation +10V to +30V Bipolar-Supply Operation ±4.5V to ±20V
- ♦ Low Power Consumption (35µW max)
- Rail-to-Rail Signal Handling
- ♦ TTL/CMOS-Logic Compatible

#### Ordering Information

PART	TEMP. RANGE	PIN-PACKAGE
DG417CJ	0°C to +70°C	8 Plastic DIP
DG417CY	0°C to +70°C	8 SO
DG417C/D	0°C to +70°C	Dice*
DG417DJ	-40°C to +85°C	8 Plastic DIP
DG417DY	-40°C to +85°C	8 SO

Ordering Information continued at end of data sheet.

### Pin Configurations/Functional Diagrams/Truth Tables



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<sup>\*</sup> Contact factory for dice specifications.

#### **ABSOLUTE MAXIMUM RATINGS**

Voltage Referenced to V-	
V+	44V
GND	25V
VL(0	SND - 0.3V) to $(V + + 0.3V)$
Digital Inputs Vs, VD (Note 1)(V-	- 2V) to (V+ + 2V) or 30mA
Continuous Current (any terminal) (No	ote 1)30mA
Peak Current, S or D (pulsed at 1ms, 10	% duty cycle max)100mA

Continuous Power Dissipation ( $T_A = +70$ °C)	
Plastic DIP (derate 9.09mW/°C above +70°	C)727mW
SO (derate 5.88mW/°C above +70°C)	471mW
CERDIP (derate 8.00mW/°C above +70°C)	640mW
Operating Temperature Ranges	
DG41_C	0°C to +70°C
DG41_D	40°C to +85°C
DG41_AK	55°C to +125°C
Storage Temperature Range	65°C to +150°C
Lead Temperature (soldering, 10sec)	+300°C

Note 1: Signals on S, D, or IN exceeding V+ or V- are clamped by internal diodes. Limit forward current to maximum current ratings.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

#### **ELECTRICAL CHARACTERISTICS—Dual Supplies**

 $(V + = +15V, V - = -15V, VL = 5V, GND = 0V, V_{INL} = 0.8V, V_{INH} = 2.4V, T_A = T_{MIN}$  to  $T_{MAX}$ , unless otherwise noted.)

PARAMETER	SYMBOL	CONDITIONS				MIN	TYP (Note 2)	MAX	UNITS	
SWITCH	1	I.				•				
Analog Signal Range	V <sub>S_</sub> , V <sub>D</sub>	(Note 3)				-15		15	V	
Drain-Source		V+ = 13.5V, V- = -13.5V,		T <sub>A</sub> = +25°C	C, D		20	35		
On-Resistance	R <sub>DS</sub> (ON)	$V_D = \pm 10V$ ,		TA = 123 C	А		20	30	Ω	
on resistance		$I_S = -10mA$		$T_A = T_{MIN}$ to T	MAX			45		
On-Resistance Match Between Channels	ΔR <sub>DS</sub> (ON)	V+ = 15V, V- = VD = ±10V,	-15V,	T <sub>A</sub> = +25°C				3	$\Omega$	
(Note 4)	AIVDS(ON)	$V_D = \pm 10V$ , $I_S = -10\text{mA}$		TA = TMIN to T	MAX			4		
On-Resistance Flatness (Note 4)	D=: .=(0.1)	V+ = 15V, V- = -15V,		TA = +25°C				4		
	RFLAT(ON)	$V_D = \pm 5V$ , $I_S = -10mA$		TA = TMIN to T	MAX			6	Ω	
Source-Off	I <sub>S(OFF)</sub>	V+ = 16.5V, V-	= -16.5V	T <sub>A</sub> = +25°C		-0.25		0.25		
Leakage Current		$V_D = \pm 15.5V,$ $V_S = \mp 15.5V$	,	TA = TMIN to	C, D	-5		5	nA	
(Note 5)				T <sub>MAX</sub>	А	-20		20		
	ID(OFF)	V+ = 16.5V, V- = -16.5V,	DG417/ DG418 DG419	$T_A = +25^{\circ}C$		-0.25	0.1	0.25		
5				TA = T <sub>MIN</sub> to	C, D	-5		5		
Drain-Off Leakage Current				Тмах	А	-20		20	nA	
(Note 5)	ID(OFF)	$V_D = \pm 15.5V$ ,		$T_A = +25^{\circ}C$		-0.75	-0.1	0.75		
		$V_S = \mp 15.5V$		$T_A = T_{MIN}$ to	C, D	-10		10		
				T <sub>MAX</sub>	А	-40		40		
			DC 417/	$T_A = +25^{\circ}C$		-0.4		0.4		
Drain-On Leakage Current (Note 5)		$V+ = 16.5V, \\ V- = -16.5V, \\ V_D = \pm 15.5V, \\ V_S = \pm 15.5V$	DG417/ DG418	TA = TMIN to	C, D	-10		10		
	I <sub>D(ON)</sub>			TMAX	А	-40		40	nA	
	(טוט)טי		DG419	$T_A = +25^{\circ}C$		-0.75		0.75		
				DG419	TA = TMIN to	C, D	-10		10	
				T <sub>MAX</sub>	Α	-40		40		

### **ELECTRICAL CHARACTERISTICS—Dual Supplies (continued)**

 $(V + = +15V, V - = -15V, VL = 5V, GND = 0V, V_{INL} = 0.8V, V_{INH} = 2.4V, T_A = T_{MIN}$  to  $T_{MAX}$ , unless otherwise noted.)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP (Note 2)	MAX	UNITS	
LOGIC INPUT	I							I.
Logic Input Current with Input Voltage High	linh	V <sub>IN</sub> = 2.4V			-0.5	0.005	0.5	μΑ
Logic Input Current with Input Voltage Low	linl	V <sub>IN</sub> = 0.8V			-0.5	0.005	0.5	μA
DYNAMIC								
Turn-On Time	ton	DG417/DG418, V <sub>D</sub> = ±10V, Figure 2		$T_A = +25^{\circ}C$ $T_A = T_{MIN} \text{ to } T_{MAX}$		100	175 250	ns
Turn-Off Time	toff	DG417/DG418, V <sub>D</sub> = ±10V, Figure 2		$T_A = +25^{\circ}C$ $T_A = T_{MIN} \text{ to } T_{MAX}$		60	145 210	ns
Transition Time	t <sub>TRANS</sub>	DG419, V <sub>S</sub> = ±10V, Figure 3		$T_A = +25^{\circ}C$ $T_A = T_{MIN} \text{ to } T_{MAX}$			175 250	ns
Break-Before-Make Interval	t <sub>D</sub>	DG419, V <sub>S1</sub> = V <sub>S2</sub> = ±10V, Figure 4, T <sub>A</sub> = +25°C		5	13		ns	
Charge Injection (Note 3)	Q	VGEN = 0V, Figure 5,	T <sub>A</sub> = +	25°C		3	10	рС
Off-Isolation Rejection Ratio (Note 6)	OIRR	$R_L = 500\Omega$ , $C_L = 5pF$ , $f = 1MHz$ , Figure 6, $T_A = +25$ °C			68		dB	
Crosstalk (Note 7)		DG419, R <sub>L</sub> = $50\Omega$ , C <sub>L</sub> = $5pF$ , f = $1MHz$ , Figure 7, T <sub>A</sub> = $+25^{\circ}C$				85		dB
Drain Off-Capacitance	C <sub>D</sub> (OFF)	$V_D = 0V$ , $f = 1MHz$ , $F$	igure 8	, T <sub>A</sub> = +25°C		8		рF
Source Off-Capacitance	C <sub>S</sub> (OFF)	$V_D = 0V$ , $f = 1MHz$ , $F$	igure 8	, T <sub>A</sub> = +25°C		8		pF
Drain-Source On-Capacitance	C <sub>D</sub> (ON)	V <sub>S</sub> = 0V, f = 1MHz, Figure 9,	DG4	17/DG418		30		pF
от варавкатов	Cs (ON)	T <sub>A</sub> = +25°C	DG41	19		35		
SUPPLY								
Positive Supply Current	+	V+ = 16.5V, V- = -16.5V, TA = +25°C	$T_A = +25^{\circ}C$	-1	-0.0001	1	μA	
1 ositive Supply Current	11	$V_{IN} = 0V \text{ or } 5V$		$T_A = T_{MIN}$ to $T_{MAX}$	-5		5	μΑ
Negative Supply Current	-	V+ = 16.5V, V- = -16.	.5V,	T <sub>A</sub> = +25°C	-1	-0.0001	1	μA
	,	$V_{IN} = 0V \text{ or } 5V$		$T_A = T_{MIN}$ to $T_{MAX}$	-5		5	μ, ,
Logic Supply Current	l IL	V+ = 16.5V, V- = -16.5V, V <sub>IN</sub> = 0V or 5V		T <sub>A</sub> = +25°C	-1	-0.0001	1	μΑ
				$T_A = T_{MIN}$ to $T_{MAX}$	-5		5	F" '
Ground Current		V+ = 16.5V, V- = -16.	6.5V, $T_A = +25^{\circ}C$		-1	-0.0001	1	μΑ
Ground Guirent		$V_{IN} = 0V \text{ or } 5V$ $T_A = T_{MIN} \text{ to } T_{MAX}$		-5		5	L ,	

#### **ELECTRICAL CHARACTERISTICS—Single Supply**

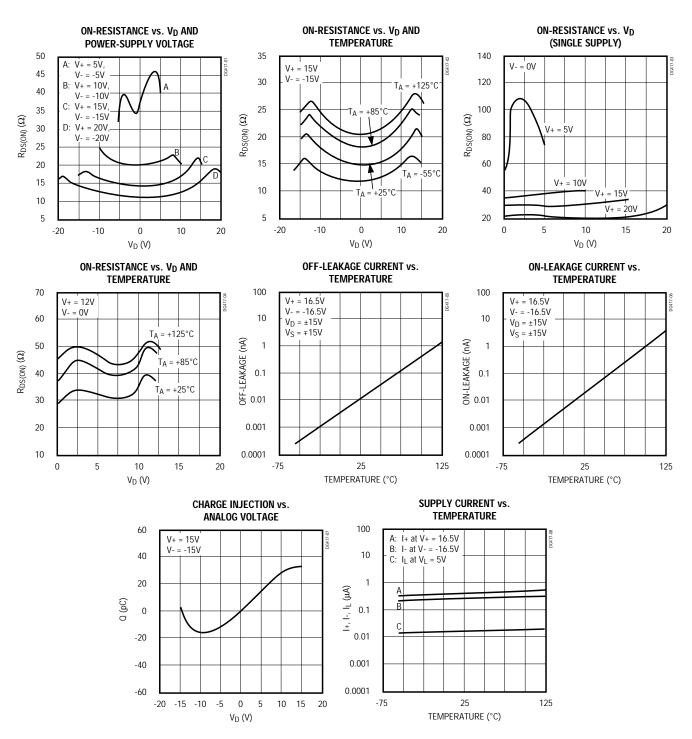
 $(V + = +12V, V - = 0V, VL = 5V, GND = 0V, V_{INH} = 2.4V, V_{INL} = 0.8V, T_A = +25°C$ , unless otherwise noted.)

PARAMETER SYMBOL		CONDITIONS		TYP (Note 2)	MAX	UNITS
SWITCH	'					1
Analog Signal Range	VANALOG	(Note 3)	0		12	V
Drain-Source On-Resistance	R <sub>DS</sub> (ON)	$I_S = -10 \text{mA}, V_D = 3.8 \text{V}, V_{+} = 10.8 \text{V}$		40	100	Ω
DYNAMIC						
Turn-On Time	t <sub>ON</sub>	DG417/DG418, V <sub>D</sub> = 8V, Figure 2		110		ns
Turn-Off Time	toff	DG417/DG418, V <sub>D</sub> = 8V, Figure 2		40		ns
Break-Before-Make Interval	t <sub>D</sub>	DG419, $R_L = 1000\Omega$ , $C_L = 35pF$ , Figure 4		60		ns
Charge Injection (Note 3)	Q	C <sub>L</sub> = 10nF, V <sub>GEN</sub> = 0V, R <sub>GEN</sub> = 0V, Figure 5		2	10	рС
SUPPLY						
Positive Supply Current	I+	All channels on or off, $V_{+} = 13.2V$ , $V_{L} = 5.25V$ , $V_{IN} = 0V$ or $5V$		-0.0001		μΑ
Negative Supply Current	I-	All channels on or off, $V+=13.2V$ , $V_L=5.25V$ , $V_{IN}=0V$ or $5V$	-0.0001		μΑ	
Logic Supply Current	IL	All channels on or off, V <sub>L</sub> = 5.25V, V <sub>IN</sub> = 0V or 5V	-0.0001		μА	
Ground Current	I <sub>GND</sub>	All channels on or off, V <sub>L</sub> = 5.25V, V <sub>IN</sub> = 0V or 5V				μА

- **Note 2:** Typical values are for **design aid only**, are not guaranteed, and are not subject to production testing. The algebraic convention where the most negative value is a minimum and the most positive value a maximum is used in this data sheet.
- Note 3: Guaranteed by design.
- **Note 4:** On-resistance match between channels and flatness is guaranteed only with bipolar-supply operation. Flatness is defined as the difference between the maximum and the minimum value of on-resistance as measured at the extremes of the specified analog range.
- Note 5: Leakage parameters I<sub>S(OFF)</sub>, I<sub>D(OFF)</sub>, and I<sub>D(ON)</sub> are 100% tested at the maximum rated hot temperature and guaranteed by correlation at +25°C.
- Note 6: Off-Isolation Rejection Ratio = 20log (V<sub>D</sub>/V<sub>S</sub>), V<sub>D</sub> = output, V<sub>S</sub> = input to off switch.
- Note 7: Between any two switches.

Typical Operating Characteristics

 $(T_A = +25^{\circ}C, \text{ unless otherwise noted.})$ 



<b>D</b> :			
Pin	Desc	rıntı	7n
_, ,,,	DCSC	ιιριι	<i>)</i>

	PIN		NAME	FUNCTION	
DG417	DG418	DG419	INAIVIE	FUNCTION	
1	_	_	S	Analog-Switch Source Terminal (normally closed)	
_	1	_	S	Analog-Switch Source Terminal (normally open)	
_	_	2	S1	Analog-Switch Source Terminal 1 (normally closed)	
2	2	_	N.C.	No Internal Connection	
3	3	3	GND	Logic Ground	
4	4	4	V+	Analog-Signal Positive Supply Input	
5	5	5	VL	Logic-Level Positive Supply Input	
6	6	6	IN	Logic-Level Input	
7	7	7	V-	Analog-Signal Negative Supply Input	
8	8	1	D	Analog-Switch Drain Terminal	
_	_	8	S2	Analog-Switch Source Terminal 2 (normally open)	

#### \_Applications Information

#### Operation with Supply Voltages Other than ±15V

Using supply voltages other than  $\pm 15V$  reduces the analog signal range. The DG417/DG418/DG419 switches operate with  $\pm 4.5V$  to  $\pm 20V$  bipolar supplies or with a  $\pm 10V$  to  $\pm 30V$  single supply; connect V- to  $\pm 30V$  single supply. Also, all device types can operate with unbalanced supplies, such as  $\pm 24V$  and  $\pm 5V$ . VL must be connected to  $\pm 5V$  to be TTL compatible, or to V+ for CMOS-logic level inputs. The Typical Operating Characteristics graphs show typical on-resistance with  $\pm 20V$ ,  $\pm 15V$ ,  $\pm 10V$ , and  $\pm 5V$  supplies. (Switching times increase by a factor of two or more for operation at  $\pm 5V$ .)

#### Overvoltage Protection

Proper power-supply sequencing is recommended for all CMOS devices. Do not exceed the absolute maximum ratings because stresses beyond the listed ratings may cause permanent damage to the devices. Always sequence V+ on first, followed by VL, V-, and logic inputs. If power-supply sequencing is not possible, add two small, external signal diodes in series with the supply pins for overvoltage protection (Figure 1).

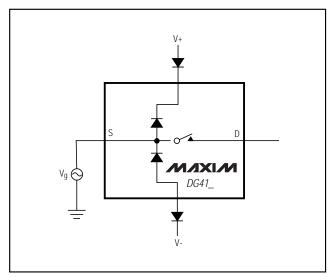


Figure 1. Overvoltage Protection Using External Blocking Diodes

Adding diodes reduces the analog signal range to 1V below V+ and 1V above V-, without affecting low switch resistance and low leakage characteristics. Device operation is unchanged, and the difference between V+ and V- should not exceed +44V.

### Test Circuits/Timing Diagrams

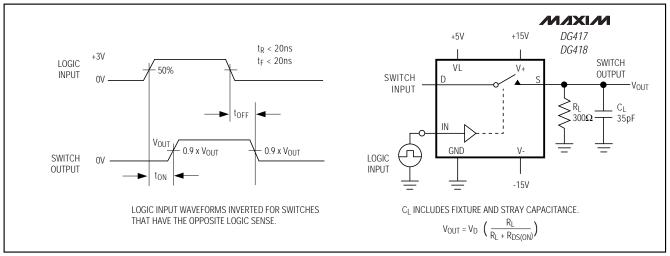


Figure 2. DG417/DG418 Switching Time

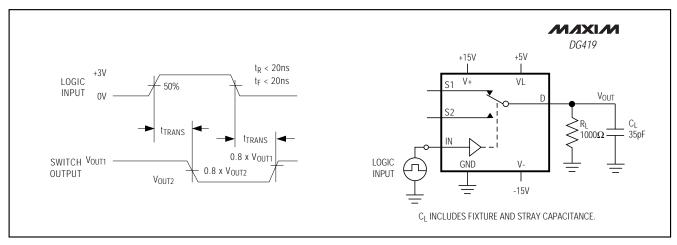


Figure 3. DG419 Transition Time

### Test Circuits/Timing Diagrams (continued)

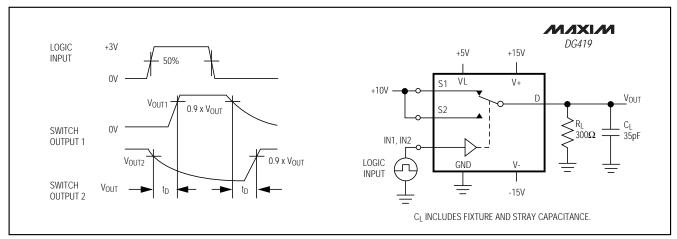


Figure 4. DG419 Break-Before-Make Interval

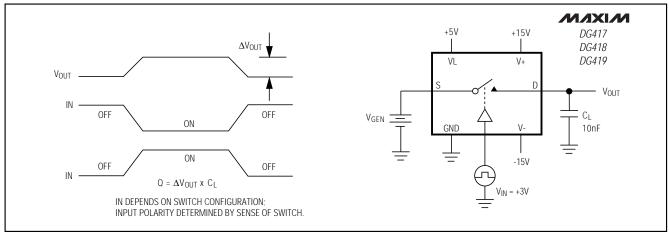


Figure 5. Charge Injection

### Test Circuits/Timing Diagrams (continued)

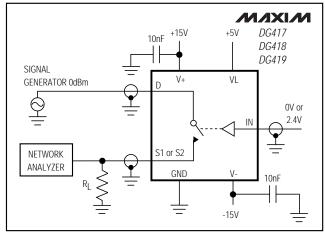


Figure 6. Off-Isolation Rejection Ratio

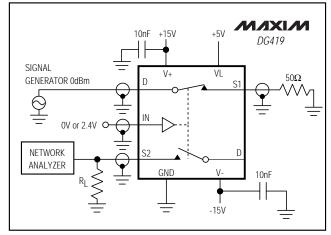


Figure 7. DG419 Crosstalk

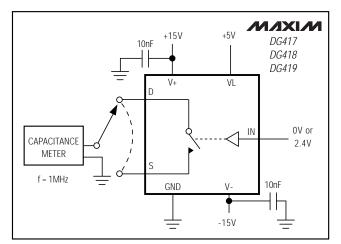


Figure 8. Drain-Source Off-Capacitance

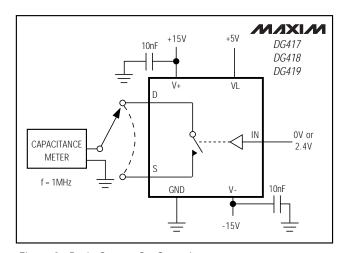


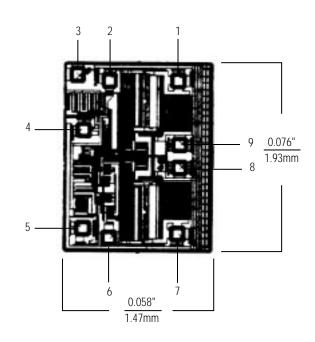
Figure 9. Drain-Source On-Capacitance

### \_Ordering Information (continued)

PART	TEMP. RANGE	PIN-PACKAGE
DG417DK	-40°C to +85°C	8 CERDIP
DG417AK	-55°C to +125°C	8 CERDIP**
DG418CJ	0°C to +70°C	8 Plastic DIP
DG418CY	0°C to +70°C	8 SO
DG418C/D	0°C to +70°C	Dice*
DG418DJ	-40°C to +85°C	8 Plastic DIP
DG418DY	-40°C to +85°C	8 SO
DG418DK	-40°C to +85°C	8 CERDIP
DG418AK	-55°C to +125°C	8 CERDIP**
DG419CJ	0°C to +70°C	8 Plastic DIP
DG419CY	0°C to +70°C	8 SO
DG419C/D	0°C to +70°C	Dice*
DG419DJ	-40°C to +85°C	8 Plastic DIP
DG419DY	-40°C to +85°C	8 SO
DG419DK	-40°C to +85°C	8 CERDIP
DG419AK	-55°C to +125°C	8 CERDIP**

<sup>\*</sup> Contact factory for dice specifications.



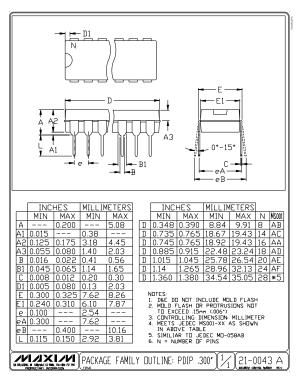


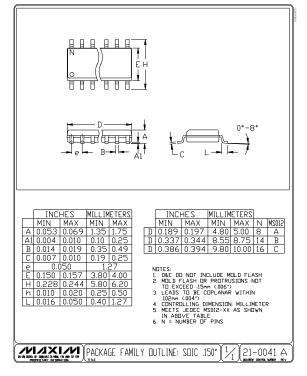
TRANSISTOR COUNT: 32 SUBSTRATE CONNECTED TO V+

DIE PAD	DG417	DG418	DG419
1	D	N.C.	S
2	GND	GND	GND
3	V+	V+	V+
4	VL	VL	VL
5	IN	IN	IN
6	V-	V-	V-
7	N.C.	S	S
8	N.C.	D	D
9	S	N.C.	D

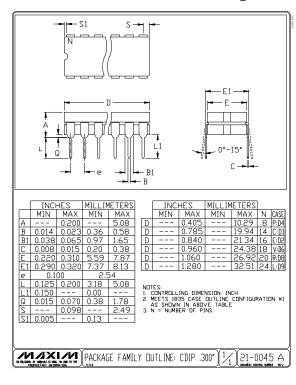
<sup>\*\*</sup>Contact factory for availability and processing to MIL-STD-883B.

Package Information





Package Information (continued)



Maxim cannot assume responsibility for use of any circuitry other than circuitry entirely embodied in a Maxim product. No circuit patent licenses are implied. Maxim reserves the right to change the circuitry and specifications without notice at any time.